

### **Amendment to the Claims**

1-16. **(Cancelled)**

17. (Previously Presented) A light-emitting diode comprising

a laminated-layer construction of semiconductor having an n-type contact layer of nitride semiconductor with an n-side electrode, a p-type contact layer of nitride semiconductor with a p-side electrode, and an active layer of nitride semiconductor,

wherein the n-side electrode and the p-side electrode are provided on the same electrode-forming-plane side,

wherein the n-type contact layer has a first area where the laminated-layer construction of semiconductor with the p-side electrode is provided, and a second area which is different from the first area as viewed from the electrode-forming-plane side,

wherein a plurality of bumps and dips is formed in the second area,

wherein a top level of the plurality of bumps and dips is positioned on the p-type contact layer side of the active layer in a cross-sectional view of the light-emitting diode, and

wherein the bottom level of the plurality of bumps and dips is positioned on the n-type contact layer side of the active layer in the cross-sectional view of the light-emitting diode.

18. (Previously Presented) The light-emitting diode according to claim 17, wherein the top level of the plurality of bumps and dips is positioned virtually as high as the p-type contact layer.

19. (Previously Presented) The light-emitting diode according to claim 17, wherein each of the bumps is formed in the shape of a trapezoid, which becomes gradually thinner in a direction toward the p-type contact layer side as viewed in a cross-sectional view of the bumps and dips.

20. (Previously Presented) The light-emitting diode according to claim 17, wherein the plurality of bumps is provided at least between the first area and the n-side electrode as viewed from the electrode-forming-plane side.

21. (Previously Presented) The light-emitting diode according to claim 17, wherein the p-side electrode has a p-side current diffusing member, which is provided on the p-type contact layer, for diffusing a current supplied thereto, and a pad member, which is provided at least on a part of the p-side current diffusing member, for supplying a current to the p-side current diffusing member, and

the laminated-layer construction of semiconductor provided in the first area, which is positioned between the n-side electrode and the pad member of the p-side electrode, has constricted portions in both sides in a direction perpendicular to a line connecting the n-side electrode and the pad member of the p-side electrode as viewed

from the electrode-forming-plane side, and the plurality of bumps and dips is formed in the constricted portions.

22. (Previously Presented) The light-emitting diode according to claim 17, wherein the p-side electrode has a p-side current diffusing member, which is provided on the p-type contact layer, for diffusing a current supplied thereto, and a pad member, which is provided at least on a part of the p-side current diffusing member, for supplying a current to the p-side current diffusing member, and

the laminated-layer construction of semiconductor provided in the first area, which is positioned between the n-side electrode and the pad member of the p-side electrode, has a portion that is constricted from the n-side electrode along a line connecting the n-side electrode and the pad member of the p-side electrode as viewed from the electrode-forming-plane side, and the plurality of bumps and dips is formed in the constricted portion.

23. (Currently Amended) The light-emitting diode according to claim ~~14~~ 17, wherein the bottom level of the plurality of bumps and dips is positioned in the n-type contact layer as viewed in a cross-section of the light-emitting diode.